## Remarks

Claims 1 and 2 are pending in the subject application and currently stand rejected. Reconsideration is respectfully requested in view of the following remarks.

Claims 1 and 2 are rejected under 35 U.S.C. §103(a) as being unpatentable over Morihara et al. (U.S. Patent No. 6,271,564) in view of Yoshida et al. (U.S. Patent No. 5,031,008) and Kakimoto et al. (U.S. Patent No. 5,166,087). Applicant respectfully traverses. Morihara et al., alone or in combination with Yoshida et al. and Kadimoto et al., fails to teach removing the nitride layer and the first oxide layer on the surface of the substrate after forming the second preliminary source/drain region through the second ion implantation process using the spacers as a mask as specified in subject claim 1. Rather, Morihara et al. teaches removing a nitride layer (insulating film 9) before performing a second ion implantation process (see col. 12, lines 12-22 and FIG. 6). Furthermore, Yoshida et al. and Kakimoto et al. fail to cure this deficiency. Accordingly, reconsideration and withdrawal of this rejection is respectfully requested.

In view of the foregoing, Applicant believes that the currently pending claims are in condition for allowance, and such action is respectfully requested.

The Commissioner is hereby authorized to charge any fees under 37 C.F.R. §§ 1.16 or 1.17 as required by this paper to Deposit Account 19-0065.

Applicant invites the Examiner to call the undersigned if clarification is needed on any of this response, or if the Examiner believes a telephonic interview would expedite the prosecution of the subject application to completion.

Respectfully submitted,

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